# UNISONIC TECHNOLOGIES CO., LTD

## UTG25N120-G2

### Insulated Gate Bipolar Transistor

# 1200V TRENCH GATE FIELD-STOP IGBT

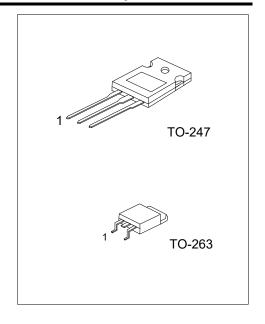
#### DESCRIPTION

The UTC **UTG25N120-G2** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

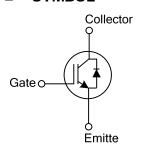
The UTC **UTG25N120-G2** is suitable for the resonant or soft switching applications.

#### **■ FEATURES**

- \* High switching speed
- \* High avalanche ruggedness
- \* Low saturation voltage: V<sub>CE(sat), typ</sub> =1.8V @ I<sub>C</sub>=25A (T<sub>C</sub> =25°C)
- \* Low switching loss:  $E_{OFF, typ}$ =2.36mJ @  $I_{C}$ =25A ( $T_{C}$  =25°C)



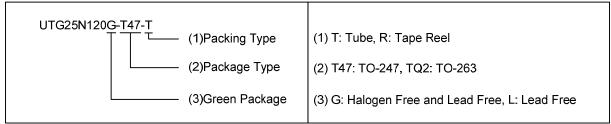
#### ■ SYMBOL



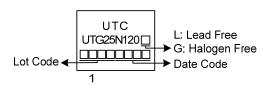
#### **■ ORDERING INFORMATION**

Ordering Number		Daakana	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG25N120L-T47-T	UTG25N120G-T47-T	TO-247	G	С	Е	Tube	
UTG25N120L-TQ2-T	UTG25N120G-TQ2-T	TO-263	G	С	E	Tube	
UTG25N120L-TQ2-R	UTG25N120G-TQ2-R	TO-263	G	С	Е	Tape Reel	

Note: Pin Assignment: G: Gate C: Collector E: Emitter



#### **■** MARKING



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#### ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	1200	V
Gate-Emitter Voltage		V <sub>GES</sub>	±20	V
Continuous Collector Current	T <sub>C</sub> =25°C	lc -	50	Α
	T <sub>C</sub> =100°C		25	Α
Collector Current Pulsed (Note 1)		I <sub>CM</sub>	100	Α
Diode Forward Current	T <sub>C</sub> =25°C	l <sub>F</sub>	50	Α
	T <sub>C</sub> =100°C		25	Α
Short Circuit Withstand Time $V_{\text{GE}} = 15\text{V}, V_{\text{CC}} \le 200\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\ge 1.0\text{s}$ $T_{\text{V,i}} = 25^{\circ}\text{C}$		tsc	10	μs
Power Dissipation (T <sub>C</sub> =25°C)	TO-247	P <sub>D</sub>	260	W
	TO-263	L,D	100	W
Operating Junction Temperature		TJ	-40 ~ +175	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +175	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

#### **■ THERMAL DATA**

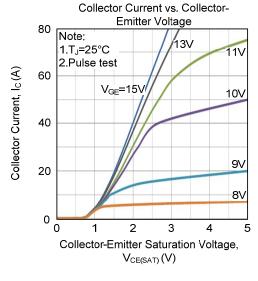
PARAMETER		SYMBOL	RATING	UNIT
Junction to Case	TO-247	0	0.48	°C/W
	TO-263	₽JC	1.25	°C/W

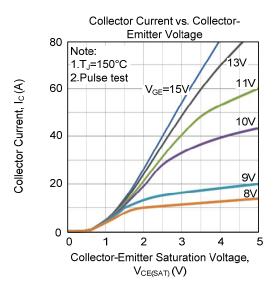
<sup>2.</sup> Pulse width limited by maximum junction temperature.

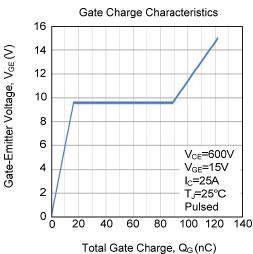
### ■ **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub>=25°C, unless otherwise noted)

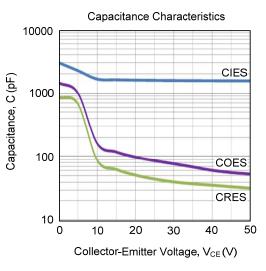
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
Off Characteristics									
Collector-Emitter Breakdown Voltage BV <sub>CES</sub>			1200			V			
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =V <sub>CES</sub> , V <sub>GE</sub> =0V			5	μΑ			
G-E Leakage Current	$I_{GES}$	V <sub>GE</sub> =V <sub>GES</sub> , V <sub>CE</sub> = 0V			±100	nA			
On Characteristics									
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	I <sub>C</sub> =250μA, V <sub>CE</sub> =V <sub>GE</sub>	4.5		7.5	V			
Calle stants Freitten Catumation Valtage		I <sub>C</sub> =25A, V <sub>GE</sub> =15V		1.8	2.1	V			
Collector to Emitter Saturation Voltage	$V_{CE(SAT)}$	I <sub>C</sub> =25A, V <sub>GE</sub> =15V, T <sub>C</sub> =125°C		2.2		V			
Dynamic Characteristics				-					
Input Capacitance	C <sub>IES</sub>			1370		pF			
Output Capacitance	C <sub>OES</sub>	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz		72.8		pF			
Reverse Transfer Capacitance	C <sub>RES</sub>			43.6		pF			
Switching Characteristics									
Total Gate Charge	$Q_G$			121.7		nC			
Gate-Emitter Charge	$Q_GE$	V <sub>CE</sub> =600V, I <sub>C</sub> =25A, V <sub>GE</sub> =15V		15.6		nC			
Gate-Collector Charge	$Q_GC$			85.6		nC			
Turn-On Delay Time	t <sub>DON)</sub>			16.7		ns			
Rise Time	$t_R$			28.4		ns			
Turn-Off Delay Time	t <sub>DOFF)</sub>	Vcc=600V, Ic=25A, R <sub>G</sub> =5Ω,		132.3		ns			
Fall Time	$t_{F}$	V <sub>GE</sub> =0~15V, L=500uH		222		ns			
Turn-On Switching Loss	Eon			2.11		mJ			
Turn-Off Switching Loss	E <sub>OFF</sub>			2.36		mJ			
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS									
Forward Voltage Drop	$V_{FM}$	I <sub>F</sub> =25A			3.5	V			
Reverse Recovery Time	t <sub>rr</sub>	125 A d1/dt-400 A/uS		50		ns			
Reverse Recovery Charge	Qrr	I <sub>F</sub> =25A, dI/dt=100A/μS		0.94		μC			

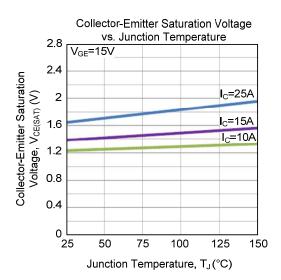
#### **■ TYPICAL CHARACTERISTICS**

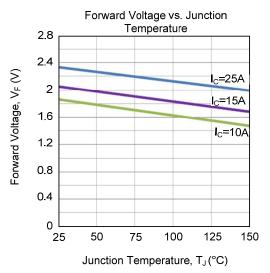




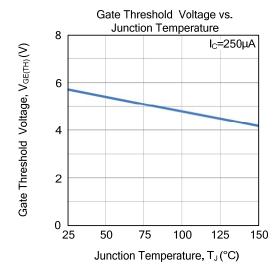


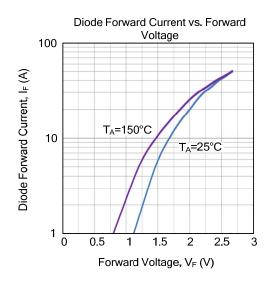


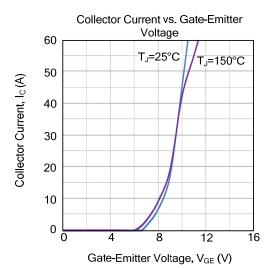


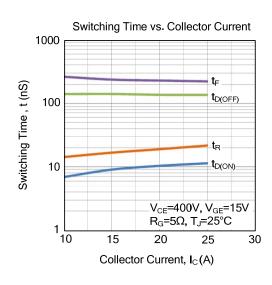


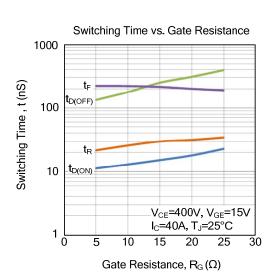
#### **■ TYPICAL CHARACTERISTICS (Cont.)**

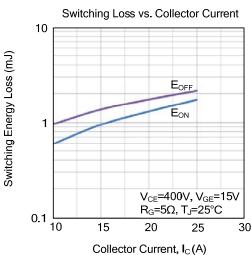




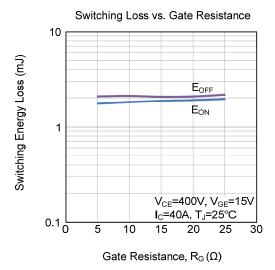


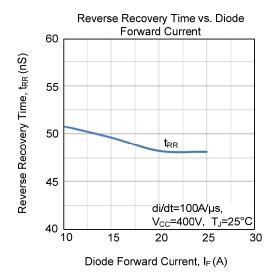


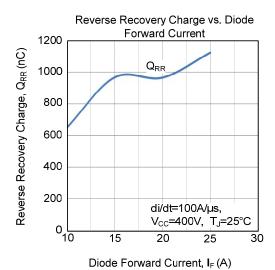


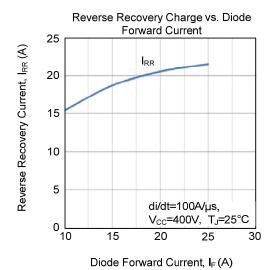


#### **■ TYPICAL CHARACTERISTICS (Cont.)**









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